

LM611 **Operational Amplifier and Adjustable Reference General Description** Features

The LM611 consists of a single-supply op-amp and a programmable voltage reference in one space saving 8-pin package. The op-amp out-performs most single-supply opamps by providing higher speed and bandwidth along with low supply current. This device was specifically designed to lower cost and board space requirements in transducer, test, measurement and data acquisition systems.

Combining a stable voltage reference with a wide output swing op-amp makes the LM611 ideal for single supply transducers, signal conditioning and bridge driving where large common-mode signals are common. The voltage reference consists of a reliable band-gap design that maintains low dynamic output impedance (1 Ω typical), excellent initial tolerance (0.6%), and the ability to be programmed from 1.2V to 6.3V via two external resistors. The voltage reference is very stable even when driving large capacitive loads, as are commonly encountered in CMOS data acquisition systems.

As a member of National's Super-Block[™] family, the LM611 is a space-saving monolithic alternative to a multi-chip solution, offering a high level of integration without sacrificing performance.

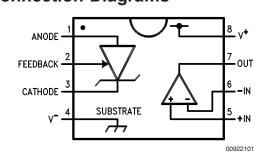
- OP AMP
- Low operating current: 300 µA (op amp)
- Wide supply voltage range: 4V to 36V
- Wide common-mode range: V⁻ to (V⁺-1.8V)
- Wide differential input voltage: ±36V
- Available in low cost 8-pin DIP
- Available in plastic package rated for Military Temperature Range Operation

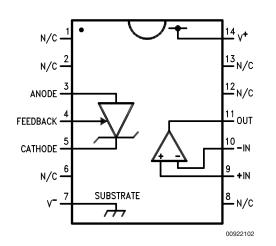
REFERENCE

- Adjustable output voltage: 1.2V to 6.3V
- Tight initial tolerance available: ±0.6%
- Wide operating current range: 17 µA to 20 mA
- Reference floats above ground
- Tolerant of load capacitance

Applications

- Transducer bridge driver
- Process and Mass Flow Control systems
- Power supply voltage monitor
- Buffered voltage references for A/D's





Connection Diagrams

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Voltage on Any Pins Except V_R	
(referred to V ⁻ pin)	36V (Max)
(Note 2)	-0.3V (Min)
Current through Any Input Pin	
and	
V _R Pin	±20 mA
Differential Input Voltage	
Military and Industrial	±36V
Commercial	±32V
Storage Temperature Range	–65°C≤T _J ≤+150°C

Maximum Junction Temperature150°CThermal Resistance, Junction-to-Ambient (Note 3)NN Package100°C/WM Package150°C/WSoldering Information Soldering (10 seconds)260°CN Package220°CESD Tolerance (Note 4)±1 kV

Operating Temperature Range

LM611AI, LM611I, LM611BI	–40°C≤T _J ≤+85°C
LM611AM, LM611M	–55°C≤T _J ≤+125°C
LM611C	0°C≤TJ≤70°C

Electrical Characteristics

These specifications apply for V⁻ = GND = 0V, V⁺ = 5V, V_{CM} = V_{OUT} = 2.5V, I_R = 100 μ A, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for T_J = 25°C; limits in **boldface type** apply over the **Operating Temperature Range.**

Symbol	Parameter Total Supply Current	Conditions $R_{LOAD} = \infty,$	Typical (Note 5) 210	LM611AM LM611AI Limits (Note 6) 300	LM611M LM611BI LM611I LM611C Limits (Note 6) 350	Units µA max
-5		$4V \le V^+ \le 36V$ (32V for LM611C)	221	320	370	µA max
Vs	Supply Voltage Range		2.2	2.8	2.8	V min
3			2.9	3	3	V min
			46	36	32	V max
			43	36	32	V max
OPERATION	AL AMPLIFIER	1		1 1		1
V _{OS1}	V _{OS} Over Supply	$4V \le V^+ \le 36V$	1.5	3.5	5.0	mV max
		$(4V \le V^+ \le 32V \text{ for LM611C})$	2.0	6.0	7.0	mV max
V _{OS2}	V _{OS} Over V _{CM}	$V_{CM} = 0V$ through $V_{CM} =$	1.0	3.5	5.0	mV max
		$(V^+ - 1.8V), V^+ = 30V, V^- = 0V$	1.5	6.0	7.0	mV max
<u>V_{OS3}</u> ΔT	Average V _{OS} Drift	(Note 6)	15			µV/°C max
I _B	Input Bias Current		10	25	35	nA max
			11	30	40	nA max
l _{os}	Input Offset Current		0.2	4	4	nA max
			0.3	5	5	nA max
I _{OS1} ΔT	Average Offset Drift Current		4			pA/°C
R _{IN}	Input Resistance	Differential	1800			MΩ
		Common-Mode	3800			MΩ
C _{IN}	Input Capacitance	Common-Mode	5.7			pF
e _n	Voltage Noise	f = 100 Hz, Input Referred	74			nV/√Hz
n	Current Noise	f = 100 Hz, Input Referred	58			fA/√Hz

Electrical Characteristics (Continued) These specifications apply for V⁻ = GND = 0V, V⁺ = 5V, V_{CM} = V_{OUT} = 2.5V, I_R = 100 μ A, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for T_J = 25°C; limits in **boldface type** apply over the **Operating Temperature Range**.

Symbol	Parameter	Conditions	Typical (Note 5)	LM611AM LM611AI Limits (Note 6)	LM611M LM611BI LM611I LM611C Limits (Note 6)	Units
OPERATIO	NAL AMPLIFIER	1	1	I		1
CMRR	Common-Mode	$V^+ = 30V, \ 0V \le V_{CM} \le (V^+ - 1.8V)$	95	80	75	dB min
	Rejection-Ratio	$CMRR = 20 \log (\Delta V_{CM} / \Delta V_{OS})$	90	75	70	dB min
PSRR	Power Supply	ower Supply $4V \le V^+ \le 30V, V_{CM} = V^+/2,$		80	75	dB min
	Rejection-Ratio	$PSRR = 20 \log (\Delta V^{+} / \Delta V_{OS})$	100	75	70	dB min
A _V	Open Loop	$R_L = 10 \text{ k}\Omega$ to GND, $V^+ = 30V$,	500	100	94	V/mV
	Voltage Gain	$5V \le V_{OUT} \le 25V$	50	40	40	min
SR	Slew Rate	V ⁺ = 30V (Note 7)	0.70	0.55	0.50	V/µs
			0.65	0.45	0.45	
GBW	Gain Bandwidth	C _L = 50 pF	0.80			MHz
			0.50			
V _{O1}	Output Voltage	$R_L = 10 \text{ k}\Omega \text{ to GND}$	V ⁺ – 1.4	V ⁺ – 1.7	V ⁺ - 1.8	V min
	Swing High	V ⁺ = 36V (32V for LM611C)	V+ – 1.6	V ⁺ – 1.9	V ⁺ – 1.9	V min
V _{O2}	Output Voltage	$R_L = 10 \text{ k}\Omega \text{ to } V^+$	V ⁻ + 0.8	V ⁻ + 0.9	V ⁻ + 0.95	V max
	Swing Low	V ⁺ = 36V (32V for LM611C)	V ⁻ + 0.9	V ⁻ + 1.0	V ⁻ + 1.0	V max
I _{out}	Output Source	$V_{OUT} = 2.5V, V_{+IN} = 0V,$	25	20	16	mA min
	Current	$V_{-IN} = -0.3V$	15	13	13	mA min
I _{SINK}	Output Sink	$V_{OUT} = 1.6V, V_{+IN} = 0V,$	17	14	13	mA min
	Current	$V_{-IN} = 0.3V$	9	8	8	mA min
SHORT	Short Circuit Current	$V_{OUT} = 0V, V_{+IN} = 3V,$	30	50	50	mA max
		$V_{-IN} = 2V$, Source	40	60	60	mA max
		$V_{OUT} = 5V, V_{+IN} = 2V,$	30	60	70	mA max
		$V_{-IN} = 3V$, Sink	32	80	90	mA max
VOLTAGE F	REFERENCE					
V _R	Reference Voltage	(Note 8)	1.244	1.2365	1.2191	V min
				1.2515	1.2689	V max
				(±0.6%)	(±2.0%)	
$\frac{\Delta V_{R}}{\Delta T_{J}}$	Average Temperature Drift	(Note 9)	10	80	150	PPM/°C max
$\frac{\Delta V_{R}}{\Delta T_{J}}$	Hysteresis	Hyst = (Vro' – Vro)/∆T _J (Note 10)	3.2			µV/°C
	V _R Change	V _{R(100 µA)} – V _{R(17 µA)}	0.05	1	1	mV max
$\frac{\Delta V_{R}}{\Delta I_{R}}$	with Current		0.1	1.1	1.1	mV max
iH		V _{R(10 mA)} - V _{R(100 µA)}	1.5	5	5	mV max
		(Note 11)	2.0	5.5	5.5	mV max
R	Resistance	∆V _{R(10→0.1 mA)} /9.9 mA	0.2	0.56	0.56	Ω max
		ΔV _{R(100→17 μA)} /83 μA	0.6	13	13	Ω max
ΔV _R	V _R Change with	$V_{R(Vro = Vr)} - V_{R(Vro = 6.3V)}$	2.5	7	7	mV max
V _{RO}	High V _{RO}	(5.06V between Anode and FEEDBACK)	2.8	10	10	mV max

Electrical Characteristics (Continued)

These specifications apply for V⁻ = GND = 0V, V⁺ = 5V, V_{CM} = V_{OUT} = 2.5V, I_R = 100 μ A, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for T_J = 25°C; limits in **boldface type** apply over the **Operating Temperature Range**.

Symbol	Parameter	Conditions	Typical (Note 5)	LM611AM LM611AI Limits (Note 6)	LM611M LM611BI LM611I LM611C Limits (Note 6)	Units
VOLTAGE R	EFERENCE					
ΔV _B	V _R Change with	$V_{R(V+ = 5V)} - V_{R(V+ = 36V)}$	0.1	1.2	1.2	mV max
$\frac{\Delta V_{R}}{\Delta V^+}$	V ⁺ Change	(V ⁺ = 32V for LM611C)	0.1	1.3	1.3	mV max
		$V_{R(V+ = 5V)} - V_{R(V+ = 3V)}$	0.01	1	1	mV max
			0.01	1.5	1.5	mV max
ΔV _R	V _R Change with	$V^+ = V^+ \max, \Delta V_R = V_R$				
ΔV_{ANODE}	V _{ANODE} Change	$(@V_{ANODE} = V^{-} = GND) - V_{R}$	0.7	1.5	1.6	mV max
AVANODE		(@ $V_{ANODE} = V^+ - 1.0V$)	3.3	3.0	3.0	mV max
I _{FB}	FEEDBACK Bias	I_{FB} ; $V_{ANODE} \le V_{FB} \le 5.06V$	22	35	50	nA max
	Current		29	40	55	nA max
e _n	V _R Noise	10 Hz to 10,000 Hz, $V_{RO} = V_R$	30			μV _{RMS}

Note 1: Absolute maximum ratings indicate limits beyond which damage to the component may occur. Electrical specifications do not apply when operating the device beyond its rated operating conditions.

Note 2: More accurately, it is excessive current flow, with resulting excess heating, that limits the voltages on all pins. When any pin is pulled a diode drop below V^- , a parasitic NPN transistor turns ON. No latch-up will occur as long as the current through that pin remains below the Maximum Rating. Operation is undefined and unpredictable when any parasitic diode or transistor is conducting.

Note 3: Junction temperature may be calculated using $T_J = T_A + P_D \theta_{JA}$. The given thermal resistance is worst-case for packages in sockets in still air. For packages soldered to copper-clad board with dissipation from one op amp or reference output transistor, nominal θ_{JA} is 90°C/W for the N package and 135°C/W for the M package.

Note 4: Human body model, 100 pF discharged through a 1.5 k Ω resistor.

Note 5: Typical values in standard typeface are for $T_J = 25^{\circ}C$; values in **boldface type** apply for the full operating temperature range. These values represent the most likely parametric norm.

Note 6: All limits are guaranteed at room temperature (standard type face) or at operating temperature extremes (bold face type).

Note 7: Slew rate is measured with op amp in a voltage follower configuration. For rising slew rate, the input voltage is driven from 5V to 25V, and the output voltage transition is sampled at 10V and 20V. For falling slew rate, the input voltage is driven from 25V to 5V, and output voltage transition is sampled at 20V and 10V. **Note 8:** V_R is the cathode-feedback voltage, nominally 1.244V.

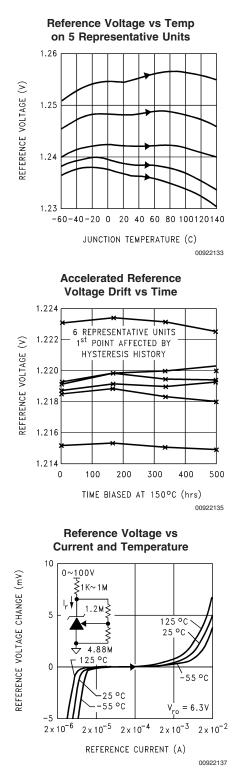
Note 9: Average reference drift is calculated from the measurement of the reference voltage at 25°C and at the temperature extremes. The drift, in ppm/°C, is $10^{6} \cdot \Delta V_{R}/(V_{R[25^{\circ}C]} \cdot \Delta T_{J})$, where ΔV_{R} is the lowest value subtracted from the highest, $V_{R[25^{\circ}C]}$ is the value at 25°C, and ΔT_{J} is the temperature range. This parameter is guaranteed by design and sample testing.

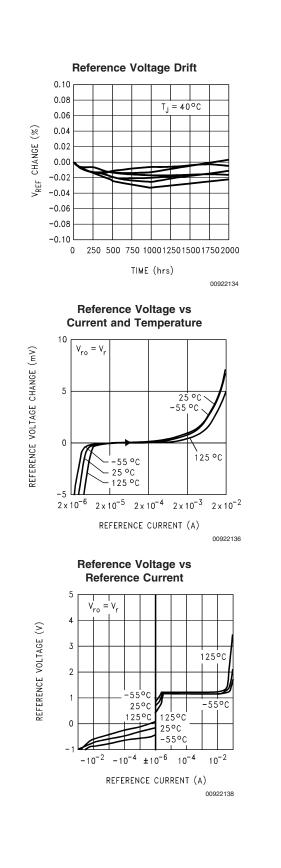
Note 10: Hysteresis is the change in V_R caused by a change in T_J , after the reference has been "dehysterized". To dehysterize the reference; that is minimize the hysteresis to the typical value, its junction temperature should be cycled in the following pattern, spiraling in toward 25°C: 25°C, 85°C, -40°C, 70°C, 0°C, 25°C. **Note 11:** Low contact resistance is required for accurate measurement.

Note 12: Military RETS 611AMX electrical test specification is available on request. The LM611AMJ/883 can also be procured as a Standard Military Drawing.

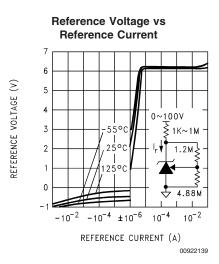
Typical Performance Characteristics (Reference)

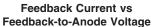
 $T_{\rm J}$ = 25°C, FEEDBACK pin shorted to V^- = 0V, unless otherwise noted

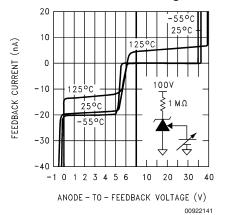




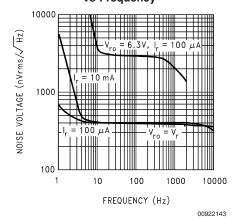


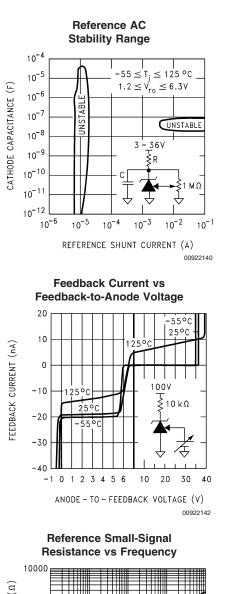


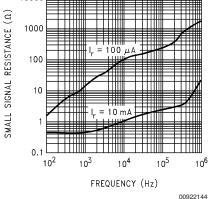




Reference Noise Voltage vs Frequency

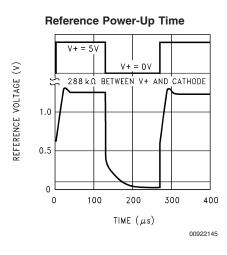




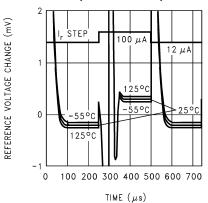


Typical Performance Characteristics (Reference) T_J = 25°C, FEEDBACK pin shorted to V⁻ =

0V, unless otherwise noted (Continued)

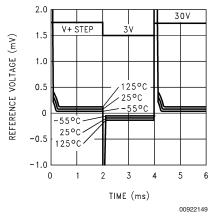


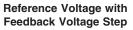
Reference Voltage with 100~12 µA Current Step

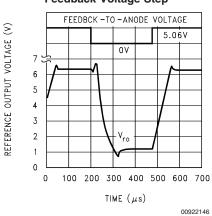


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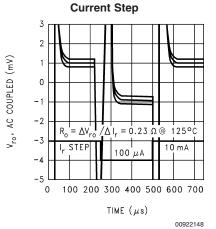
Reference Voltage Change with Supply Voltage Step





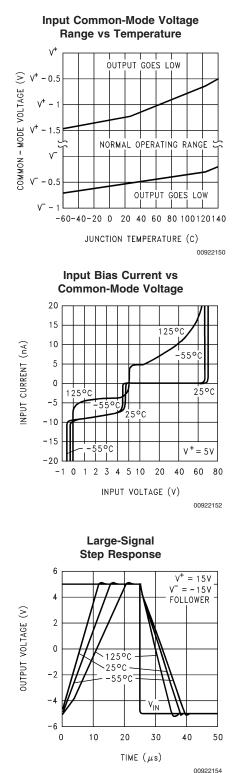


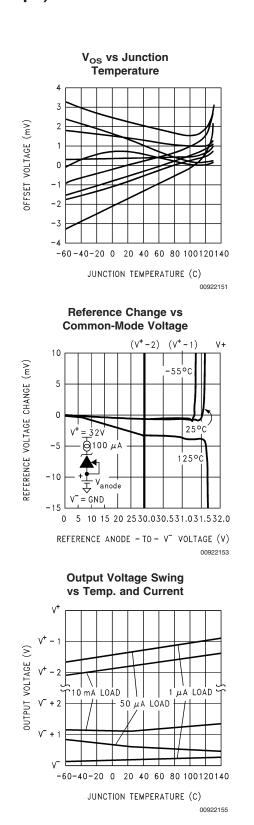
Reference Step Response for 100 μ A ~ 10 mA

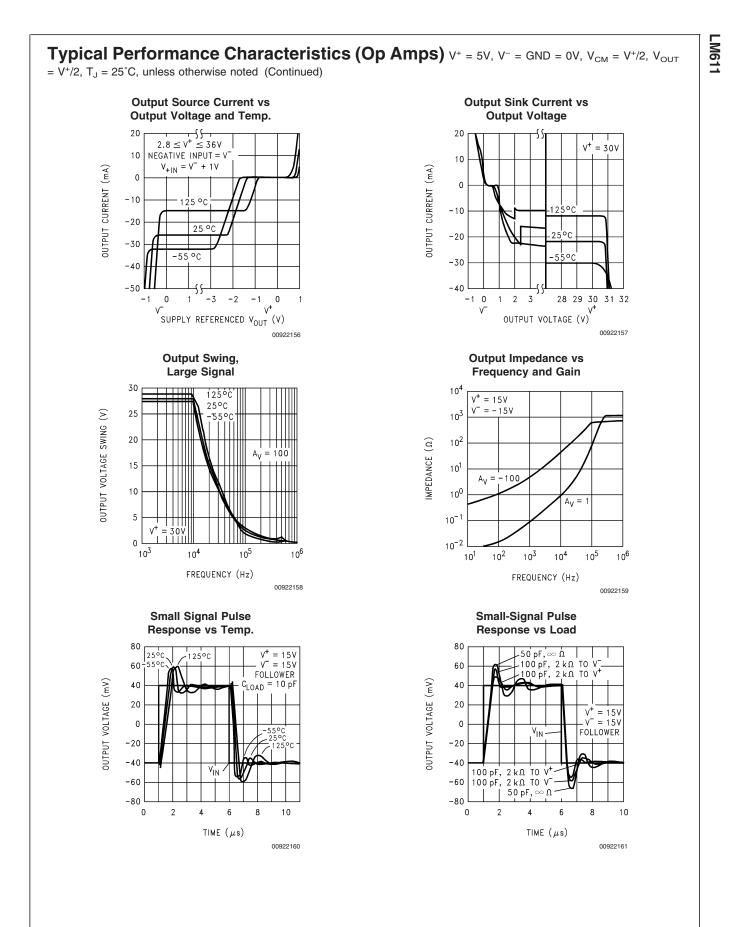


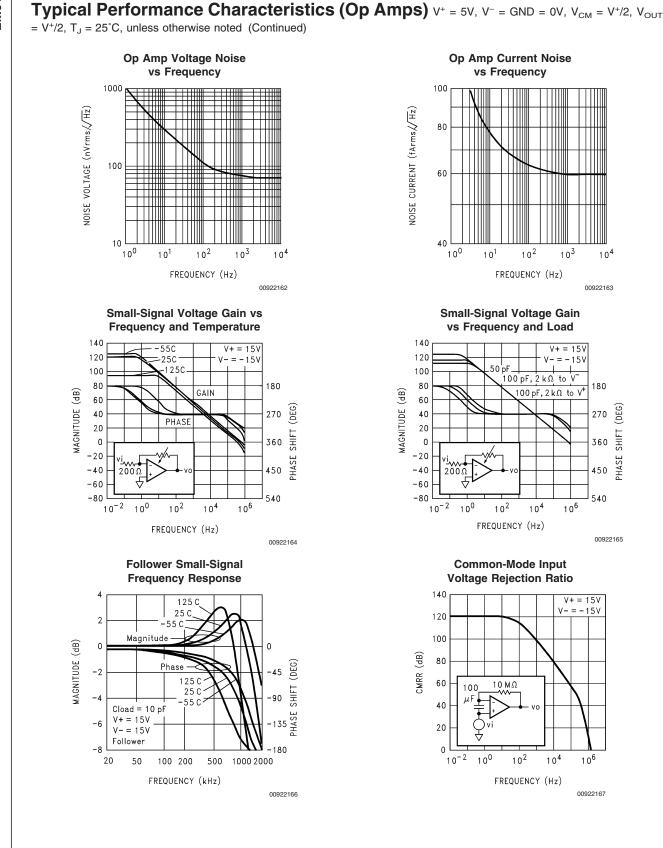
Typical Performance Characteristics (Op Amps)

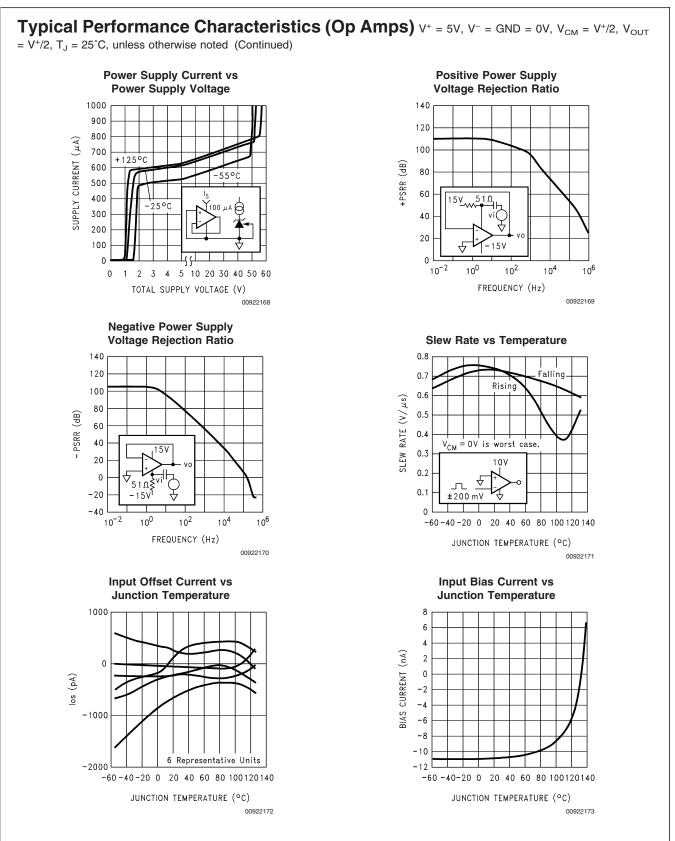
V^+ = 5V, V^- = GND = 0V, V_{CM} = V^+/2, V_{OUT} = V^+/2, T_J = 25°C, unless otherwise noted





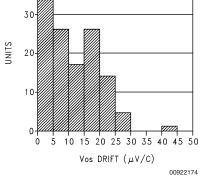


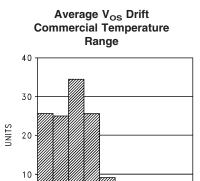






Typical Performance Distributions Average V_{os} Drift Military Temperature Range

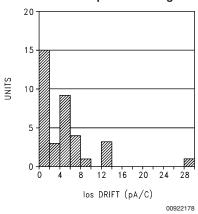




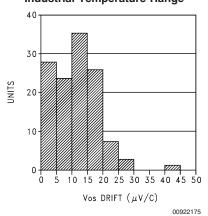
0 5 10 15 20 25 30 35 40 45 50 Vos DRIFT (μV/C) 00922176

0

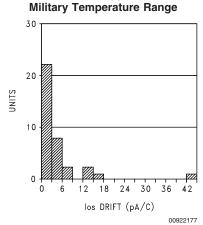
Average I_{OS} Drift Industrial Temperature Range



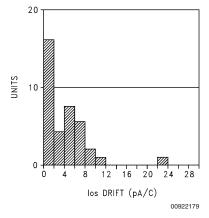
Average V_{OS} Drift Industrial Temperature Range

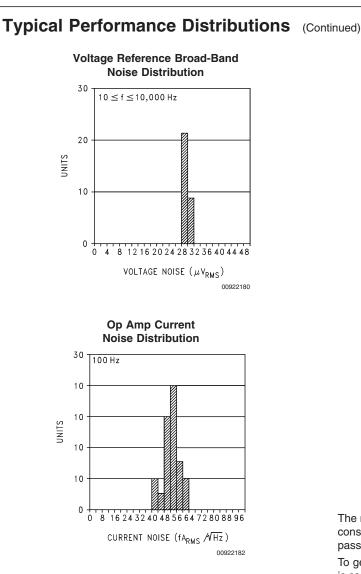


Average I_{OS} Drift



Average I_{OS} Drift Commercial Temperature Range





Application Information

VOLTAGE REFERENCE

Reference Biasing

The voltage reference is of a shunt regulator topology that models as a simple zener diode. With current I_r flowing in the 'forward' direction there is the familiar diode transfer function. I_r flowing in the reverse direction forces the reference voltage to be developed from cathode to anode. The applied voltage to the cathode may range from a diode drop below V⁻ to the reference voltage or to the avalanche voltage of the parallel protection diode, nominally 7V. A 6.3V reference with V+ = 3V is allowed.

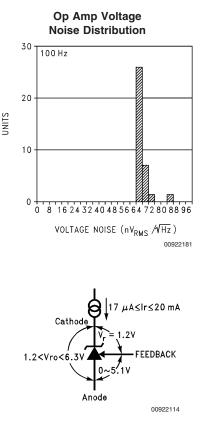


FIGURE 1. Voltages Associated with Reference (Current Source I, is External)

The reference equivalent circuit reveals how V_r is held at the constant 1.2V by feedback, and how the FEEDBACK pin passes little current.

To generate the required reverse current, typically a resistor is connected from a supply voltage higher than the reference voltage. Varying that voltage, and so varying I_r , has small effect with the equivalent series resistance of less than an ohm at the higher currents. Alternatively, an active current source, such as the LM134 series, may generate I_r .

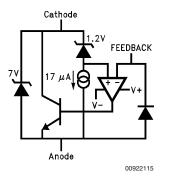


FIGURE 2. Reference Equivalent Circuit

Application Information (Continued)

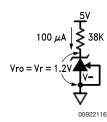


FIGURE 3. 1.2V Reference

Capacitors in parallel with the reference are allowed. See the Reference AC Stability Range curve for capacitance values—from 20 μ A to 3 mA any capacitor value is stable. With the reference's wide stability range with resistive and capacitive loads, a wide range of RC filter values will perform noise filtering.

Adjustable Reference

The FEEDBACK pin allows the reference output voltage, V_{ro}, to vary from 1.24V to 6.3V. The reference attempts to hold V_r at 1.24V. If V_r is above 1.24V, the reference will conduct current from Cathode to Anode; FEEDBACK current always remains low. If FEEDBACK is connected to Anode, then V_{ro} = V_r = 1.24V. For higher voltages FEEDBACK is held at a constant voltage above Anode—say 3.76V for V_{ro} = 5V. Connecting a resistor across the constant V_r generates a current I=R1/V_r flowing from Cathode into FEEDBACK node. A Thevenin equivalent 3.76V is generated from FEEDBACK to Anode with R2=3.76/I. Keep I greater than one thousand times larger than FEEDBACK bias current for <0.1% error—I≥32 µA for the military grade over the military temperature range (I≥5.5 µA for a 1% untrimmed error for a commercial part.)

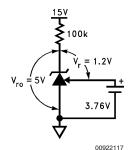


FIGURE 4. Thevenin Equivalent of Reference with 5V Output

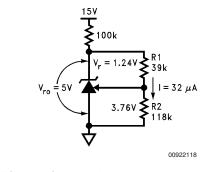




FIGURE 5. Resistors R1 and R2 Program Reference Output Voltage to be 5V

Understanding that V_r is fixed and that voltage sources, resistors, and capacitors may be tied to the FEEDBACK pin, a range of V_r temperature coefficients may be synthesized.

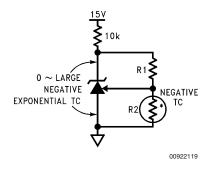


FIGURE 6. Output Voltage has Negative Temperature Coefficient (TC) if R2 has Negative TC

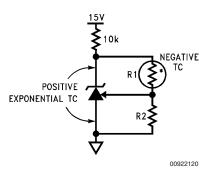


FIGURE 7. Output Voltage has Positive TC if R1 has Negative TC

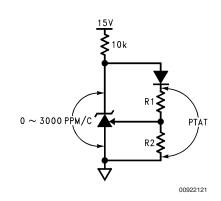
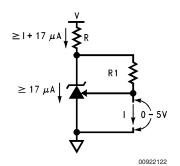


FIGURE 8. Diode in Series with R1 Causes Voltage Across R1 and R2 to be Proportional to Absolute Temperature (PTAT)

Connecting a resistor across Cathode-to-FEEDBACK creates a 0 TC current source, but a range of TCs may be synthesized.

Application Information (Continued)



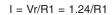


FIGURE 9. Current Source is Programmed by R1

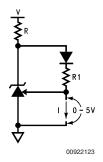


FIGURE 10. Proportional-to-Absolute-Temperature Current Source

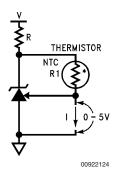


FIGURE 11. Negative -TC Current Source

Hysteresis

The reference voltage depends, slightly, on the thermal history of the die. Competitive micro-power products vary—always check the data sheet for any given device. Do not assume that no specification means no hysteresis.

OPERATIONAL AMPLIFIER

The amp or the reference may be biased in any way with no effect on the other, except when a substrate diode conducts (see Guaranteed Electrical Characteristics Note 1). The amp may have inputs outside the common-mode range, may be operated as a comparator, or have all terminals floating with no effect on the reference (tying inverting input to output and non-inverting input to V⁻ on unused amp is preferred). Choosing operating points that cause oscillation, such as driving too large a capacitive load, is best avoided.

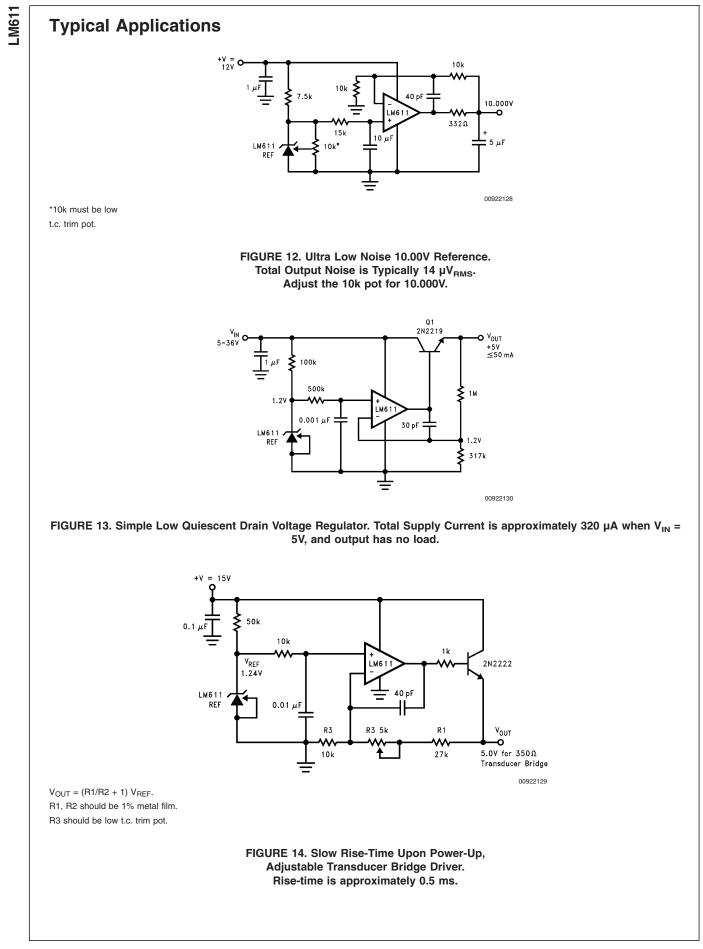
Op Amp Output Stage

The op amp, like the LM124 series, has a flexible and relatively wide-swing output stage. There are simple rules to optimize output swing, reduce cross-over distortion, and optimize capacitive drive capability:

- Output Swing: Unloaded, the 42 μA pull-down will bring the output within 300 mV of V⁻ over the military temperature range. If more than 42 μA is required, a resistor from output to V⁻ will help. Swing across any load may be improved slightly if the load can be tied to V⁺, at the cost of poorer sinking open-loop voltage gain.
- 2. Cross-over Distortion: The LM611 has lower cross-over distortion (a 1 V_{BE} deadband versus 3 V_{BE} for the LM124), and increased slew rate as shown in the characteristic curves. A resistor pull-up or pull-down will force class-A operation with only the PNP or NPN output transistor conducting, eliminating cross-over distortion.
- 3. Capacitive Drive: Limited by the output pole caused by the output resistance driving capacitive loads, a pull-down resistor conducting 1 mA or more reduces the output stage NPN r_e until the output resistance is that of the current limit 25 Ω . 200 pF may then be driven without oscillation.

Op Amp Input Stage

The lateral PNP input transistors, unlike those of most op amps, have BV_{EBO} equal to the absolute maximum supply voltage. Also, they have no diode clamps to the positive supply nor across the inputs. These features make the inputs look like high impedances to input sources producing large differential and common-mode voltages.



Typical Applications (Continued)

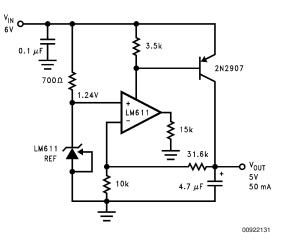


FIGURE 15. Low Drop-Out Voltage Regulator Circuit. Drop out voltage is typically 0.2V.

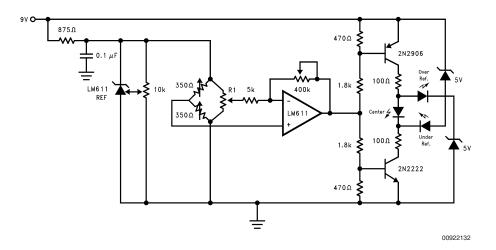
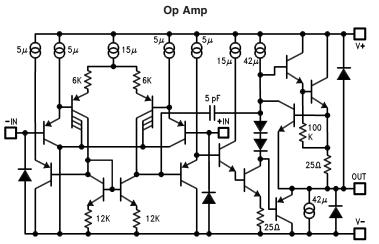


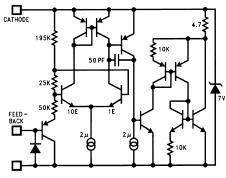
FIGURE 16. Nulling Bridge Detection System. Adjust sensitivity via 400 k $\!\Omega$ pot. Null offset with R1, and bridge drive with the 10k pot.

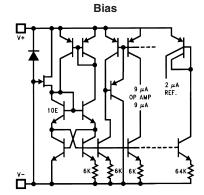
Simplified Schematic Diagrams











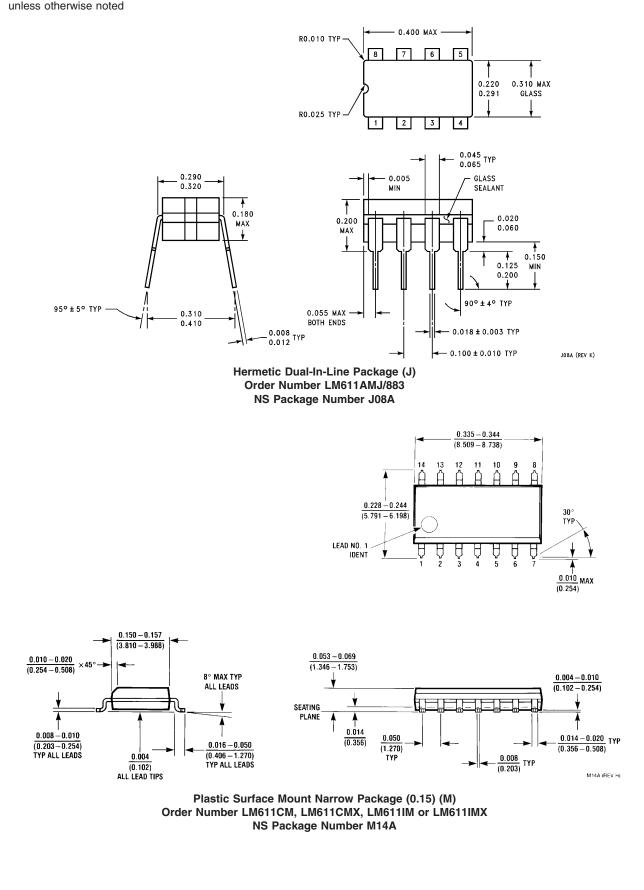
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Ordering Information

Reference	Tem	Package	NSC		
Tolerance & V _{os}	Military	Industrial	Industrial Commercial		Drawing
	–55°C≤T _A ≤+125°C	–40°C≤T _A ≤+85°C	0°C≤T _A ≤+70°C		
±0.6% @	LM611AMJ/883 (Note 12)	—	—	8-pin	J08A
80 ppm/°C max				ceramic DIP	
V_{OS} = 3.5 mV max					
±2.0% @	_	LM611IM	LM611CM	14-pin Narrow	M14A
150 ppm/°C max		LM611IMX	LM611CMX	Surface Mount	
$V_{OS} = 5 \text{ mV max}$					





Notes

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